

TM013H02S

N+N-Channel Enhancement Mode Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

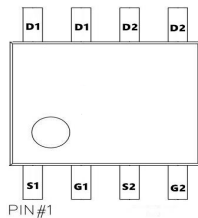
Product Summary

$V_{DS} = 20V$ $I_D = 10A$

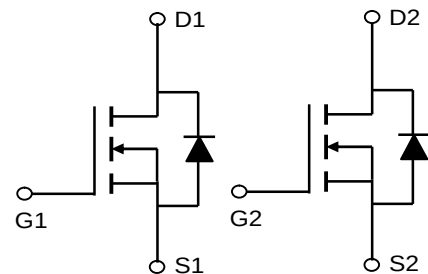
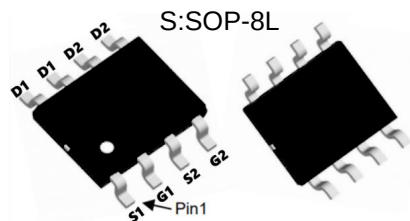
$R_{DS(ON)} = 13m\Omega (typ.) @ V_{GS} = 4.5V$

100% UIS Tested

100% R_g Tested



Marking: 10V02 OR 9928



Absolute Maximum Rating ($T_A = 25^\circ C$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A = 25^\circ C$	I_D	10	A
Pulsed Drain Current ¹		I_{DM}	28	A
Power Dissipation	$T_A = 25^\circ C$	P_D	2.25	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	80	$^\circ C/W$

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	20	-	-	V
Gate Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V	-	-	±100	nA
Drain Cut-off Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V	-	-	1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	0.45	0.7	1	V
Drain-Source On-State Resistance ³	R _{DS(on)}	V _{GS} = 4.5V, I _D =5A	-	13	20	mΩ
		V _{GS} = 2.5V, I _D = 4.7A	-	18	30	
		V _{GS} = 1.8V, I _D = 4.3A	-	28	57	
Dynamic Characteristics ⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz	-	700	-	pF
Output Capacitance	C _{oss}		-	120	-	
Reverse Transfer Capacitance	C _{rss}		-	105	-	
Switching Characteristics ⁴						
Total Gate Charge	Q _g	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 5A	-	10.5	-	nC
Gate-Source Charge	Q _{gs}		-	2	-	
Gate-Drain Charge	Q _{gd}		-	2.5	-	
Turn-On Time	t _{d(on)}	V _{GS} = 5V, V _{DD} = 10V, I _D = 5A,R _G = 3Ω,	-	10	-	ns
Rise Time	t _r		-	20	-	
Turn-Off Time	t _{d(off)}		-	32	-	
Fall Time	t _f		-	12	-	
Source-Drain Diode Characteristics						
Body Diode Voltage ³	V _{SD}	I _S =4A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	I _S		-	-	10	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
2. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. This value is guaranteed by design hence it is not included in the production test.

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Typical Characteristics

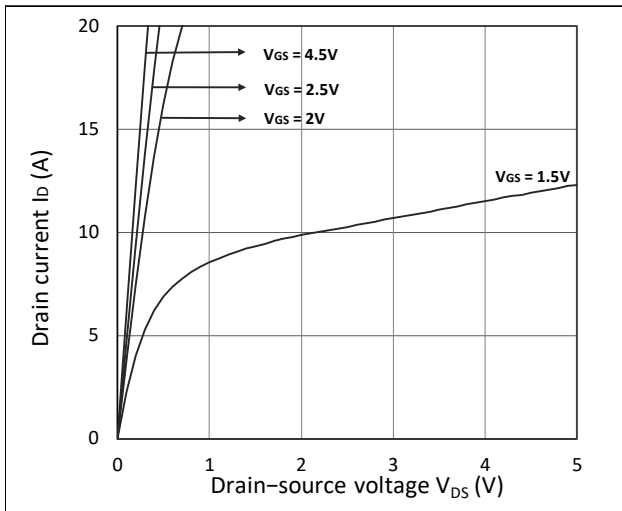


Figure 1. Output Characteristics

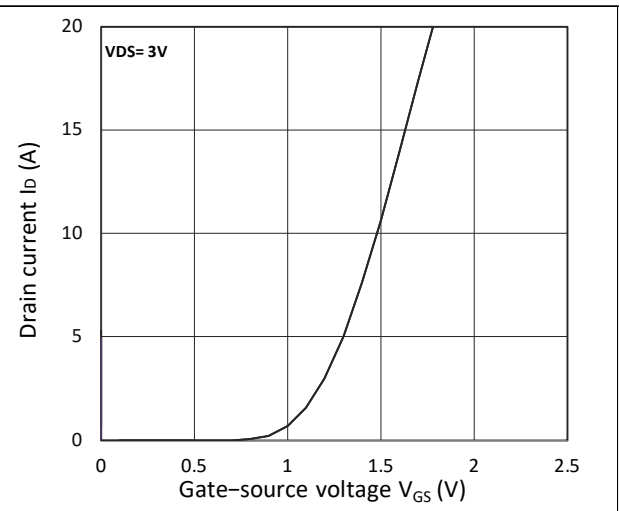


Figure 2. Transfer Characteristics

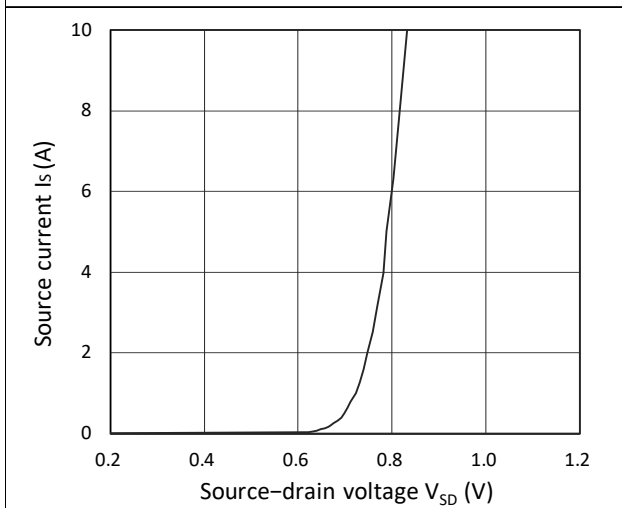


Figure 3. Forward Characteristics of Reverse

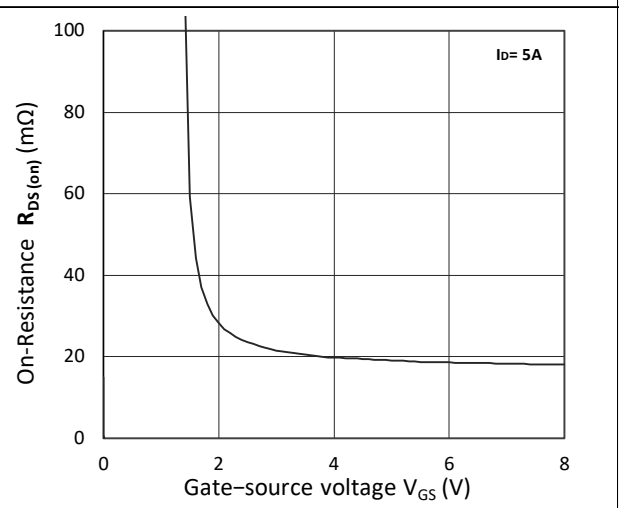


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

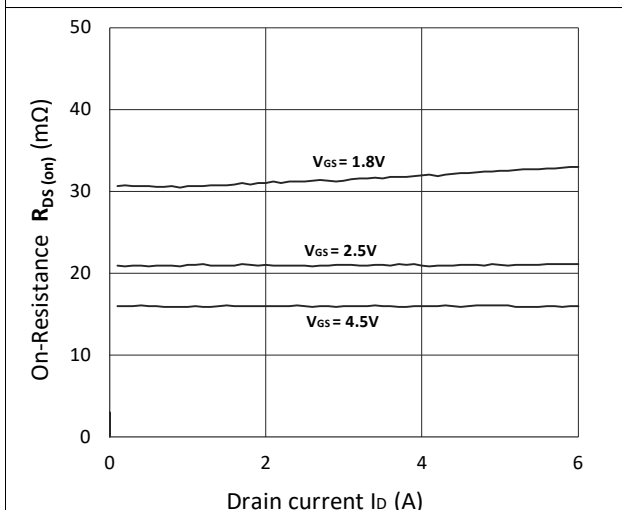


Figure 5. $R_{DS(ON)}$ vs. I_D

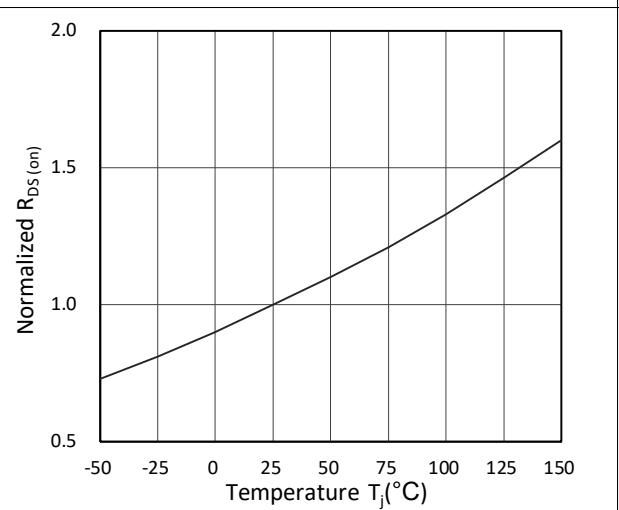


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature



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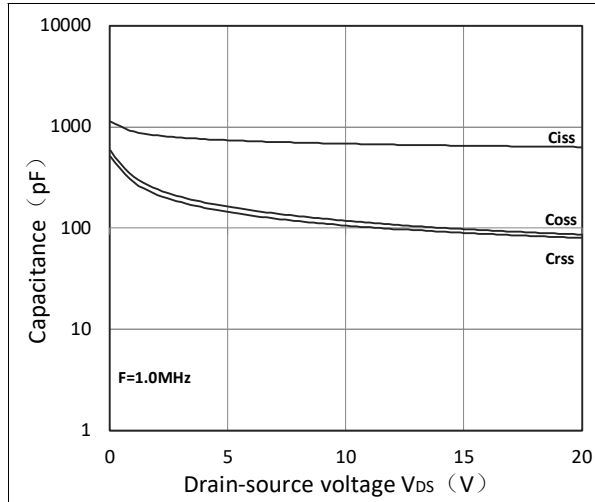


Figure 7. Capacitance Characteristics

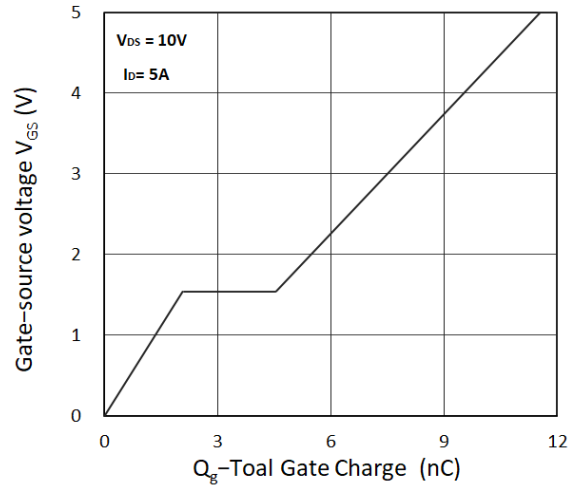
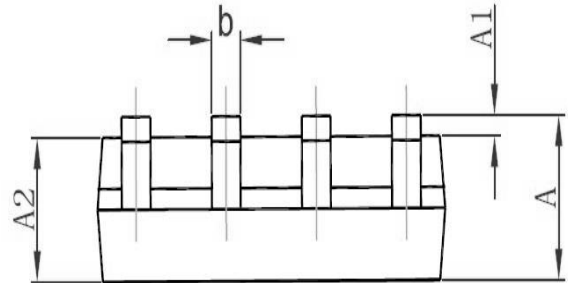
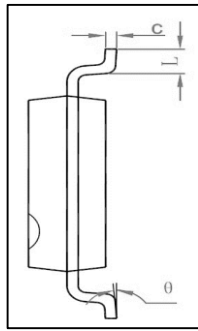
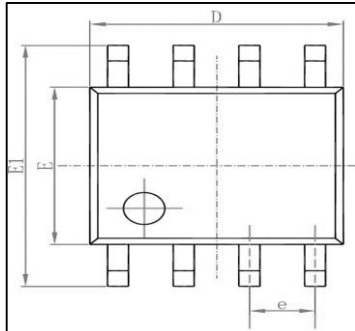
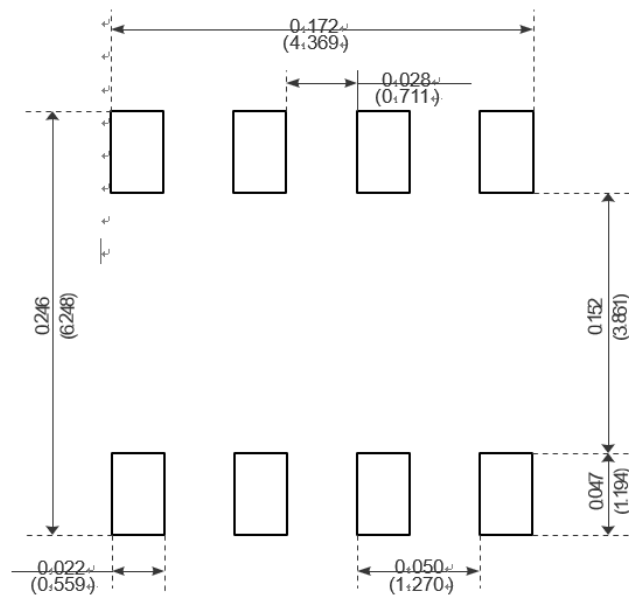


Figure 8. Gate Charge Characteristics

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads